Tien-chang Lu

List of Publications by Year
in descending order

411	6,946	71061	102432
papers	citations	41 h-index	66 g-index

413	413	413	4858
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	CW lasing of current injection blue GaN-based vertical cavity surface emitting laser. Applied Physics Letters, 2008, 92, .	1.5	247
2	Enhancing the output power of GaN-based LEDs grown on wet-etched patterned sapphire substrates. IEEE Photonics Technology Letters, 2006, 18, 1152-1154.	1.3	231
3	Hole injection and efficiency droop improvement in InGaN/GaN light-emitting diodes by band-engineered electron blocking layer. Applied Physics Letters, 2010, 97, 261103.	1.5	190
4	Low efficiency droop in blue-green m-plane InGaN/GaN light emitting diodes. Applied Physics Letters, 2010, 96, .	1.5	149
5	Continuous wave operation of current injected GaN vertical cavity surface emitting lasers at room temperature. Applied Physics Letters, 2010, 97, .	1.5	140
6	Hole transport improvement in InGaN/GaN light-emitting diodes by graded-composition multiple quantum barriers. Applied Physics Letters, 2011, 99, .	1.5	123
7	Nanoscale epitaxial lateral overgrowth of GaN-based light-emitting diodes on a SiO2 nanorod-array patterned sapphire template. Applied Physics Letters, 2008, 93, .	1.5	113
8	Study of the Excitation Power Dependent Internal Quantum Efficiency in InGaN/GaN LEDs Grown on Patterned Sapphire Substrate. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1137-1143.	1.9	113
9	Strong lightâ€“matter interaction in ZnO microcavities. Light: Science and Applications, 2013, 2, e76-e76.	7.7	112
10	High-Operation-Temperature Plasmonic Nanolasers on Single-Crystalline Aluminum. Nano Letters, 2016, 16, 3179-3186.	4.5	110
11	Fabrication of InGaN/GaN nanorod light-emitting diodes with self-assembled Ni metal islands. Nanotechnology, 2007, 18, 445201.	1.3	100
12	Ultrastrong Mode Confinement in ZnO Surface Plasmon Nanolasers. ACS Nano, 2015, 9, 3978-3983.	7.3	95
13	Room temperature polariton lasing vs photon lasing in a ZnO-based hybrid microcavity. Optics Express, 2012, 20, 5530.	1.7	94
14	Structural Colors Enabled by Lattice Resonance on Silicon Nitride Metasurfaces. ACS Nano, 2020, 14, 5678-5685.	7.3	91
15	Crack-free GaNâˆ•AlN distributed Bragg reflectors incorporated with GaNâˆ•AlN superlattices grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2006, 88, 061904.	1.5	89
16	Temperature-Dependent Electroluminescence Efficiency in Blue InGaNâ€“GaN Light-Emitting Diodes With Different Well Widths. IEEE Photonics Technology Letters, 2010, 22, 236-238.	1.3	85
17	Flexible Organometalâ€“Halide Perovskite Lasers for Speckle Reduction in Imaging Projection. ACS Nano, 2019, 13, 5421-5429.	7.3	84
18	GaN-based two-dimensional surface-emitting photonic crystal lasers with AlNâˆ•GaN distributed Bragg reflector. Applied Physics Letters, 2008, 92, .	1.5	81

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19	Efficiency Enhancement and Beam Shaping of GaNâ€“InGaN Vertical-Injection Light-Emitting Diodes via High-Aspect-Ratio Nanorod Arrays. IEEE Photonics Technology Letters, 2009, 21, 257-259.	1.3	81
20	Enhanced light output of an InGaN/GaN light emitting diode with a nano-roughened p-GaN surface. Nanotechnology, 2005, 16, 1844-1848.	1.3	80
21	Efficiency droop alleviation in InGaN/GaN light-emitting diodes by graded-thickness multiple quantum wells. Applied Physics Letters, 2010, 97, .	1.5	76
22	Broadband and omnidirectional antireflection employing disordered GaN nanopillars. Optics Express, 2008, 16, 8748.	1.7	75
23	Fabrication and performance of blue GaN-based vertical-cavity surface emitting laser employing AlNâˆ•GaN and Ta2O5âˆ•SiO2 distributed Bragg reflector. Applied Physics Letters, 2005, 87, 081105.	1.5	62
24	Lasing behaviors upon phase transition in solution-processed perovskite thin films. Applied Physics Letters, 2014, 105, .	1.5	59
25	Lowâ€Threshold Bound State in the Continuum Lasers in Hybrid Lattice Resonance Metasurfaces. Laser and Photonics Reviews, 2021, 15, 2100118.	4.4	59
26	Single-crystalline aluminum film for ultraviolet plasmonic nanolasers. Scientific Reports, 2016, 6, 19887.	1.6	58
27	Ultracompact Pseudowedge Plasmonic Lasers and Laser Arrays. Nano Letters, 2018, 18, 747-753.	4.5	56
28	Effects of Built-In Polarization and Carrier Overflow on InGaN Quantum-Well Lasers With Electronic Blocking Layers. Journal of Lightwave Technology, 2008, 26, 329-337.	2.7	55
29	Progress and prospects of GaN-based VCSEL from near UV to green emission. Progress in Quantum Electronics, 2018, 57, 1-19.	3.5	54
30	Study on optimal growth conditions of a-plane GaN grown on r-plane sapphire by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2007, 300, 308-313.	0.7	52
31	Enhanced light output from a nitride-based power chip of green light-emitting diodes with nano-rough surface using nanoimprint lithography. Nanotechnology, 2008, 19, 185301.	1.3	50
32	ZnO nanopowders fabricated by dc thermal plasma synthesis. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2006, 134, 54-58.	1.7	48
33	Optical properties of a-plane InGaN/GaN multiple quantum wells on r-plane sapphire substrates with different indium compositions. Journal of Applied Physics, 2009, 105, .	1.1	48
34	Investigation of wavelength-dependent efficiency droop in InGaN light-emitting diodes. Applied Physics B: Lasers and Optics, 2010, 98, 779-789.	1.1	48
35	High Light-Extraction GaN-Based Vertical LEDs With Double Diffuse Surfaces. IEEE Journal of Quantum Electronics, 2006, 42, 1196-1201.	1.0	47
36	Efficiency and Droop Improvement in GaN-Based High-Voltage Light-Emitting Diodes. IEEE Electron Device Letters, 2011, 32, 1098-1100.	2.2	46

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37	Manipulation of nanoscale V-pits to optimize internal quantum efficiency of InGaN multiple quantum wells. Applied Physics Letters, 2015, 106, .	1.5	46
38	High Brightness GaN-Based Light-Emitting Diodes. Journal of Display Technology, 2007, 3, 118-125.	1.3	43
39	Plasmonic Nanolasers Enhanced by Hybrid Grapheneâ€“Insulatorâ€“Metal Structures. Nano Letters, 2019, 19, 5017-5024.	4.5	43
40	Dichromatic InGaN-based white light emitting diodes by using laser lift-off and wafer-bonding schemes. Applied Physics Letters, 2007, 90, 161115.	1.5	42
41	High output power density from GaN-based two-dimensional nanorod light-emitting diode arrays. Applied Physics Letters, 2009, 94, 141111.	1.5	42
42	Fabrication and Characterization of GaN-Based LEDs Grown on Chemical Wet-Etched Patterned Sapphire Substrates. Journal of the Electrochemical Society, 2006, 153, G1106.	1.3	41
43	Numerical study of optical properties of InGaN multi-quantum-well laser diodes with polarization-matched AlInGaN barrier layers. Applied Physics B: Lasers and Optics, 2009, 95, 145-153.	1.1	40
44	Reduction of Efficiency Droop in Semipolar (1ar101) InGaN/GaN Light Emitting Diodes Grown on Patterned Silicon Substrates. Applied Physics Express, 2011, 4, 012105.	1.1	39
45	Large vacuum Rabi splitting in ZnO-based hybrid microcavities observed at room temperature. Applied Physics Letters, 2009, 94, 061103.	1.5	38
46	Sub-wavelength GaN-based membrane high contrast grating reflectors. Optics Express, 2012, 20, 20551.	1.7	38
47	A novel randomly textured phosphor structure for highly efficient white light-emitting diodes. Nanoscale Research Letters, 2012, 7, 188.	3.1	38
48	High density GaN/AlN quantum dots for deep UV LED with high quantum efficiency and temperature stability. Scientific Reports, 2014, 4, 5166.	1.6	38
49	Effect of Controlled Growth Dynamics on the Microstructure of Nonpolara-Plane GaN Revealed by X-ray Diffraction. Japanese Journal of Applied Physics, 2009, 48, 071002.	0.8	37
50	High efficiency GaN-based light-emitting diodes with embedded air voids/SiO₂nanomasks. Nanotechnology, 2012, 23, 045303.	1.3	37
51	Enhancement of InGaNâ€“GaN Indiumâ€“Tinâ€“Oxide Flip-Chip Light-Emitting Diodes With TiO$_2$â€“SiO$_2$Multilayer Stack Omnidirectional Reflector. IEEE Photonics Technology Letters, 2006, 18, 2050-2052.	1.3	36
52	The characteristics of the high-ÂEr2O3 (erbium oxide) dielectrics deposited on polycrystalline silicon. Solid State Communications, 2012, 152, 504-508.	0.9	36
53	Room-Temperature Operation of Optically Pumped Blue-Violet GaN-Based Vertical-Cavity Surface-Emitting Lasers Fabricated by Laser Lift-Off. Japanese Journal of Applied Physics, 2006, 45, 2556-2560.	0.8	35
54	Optically Pumped GaN-based Vertical Cavity Surface Emitting Lasers: Technology and Characteristics. Japanese Journal of Applied Physics, 2007, 46, 5397.	0.8	35

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55	Study of GaN-Based Light-Emitting Diodes Grown on Chemical Wet-Etching-Patterned Sapphire Substrate With V-Shaped Pits Roughening Surfaces. Journal of Lightwave Technology, 2008, 26, 1455-1463.	2.7	35
56	3D numerical modeling of the carrier transport and radiative efficiency for InGaN/GaN light emitting diodes with V-shaped pits. AIP Advances, 2016, 6, .	0.6	35
57	Characteristics of efficiency droop in GaN-based light emitting diodes with an insertion layer between the multiple quantum wells and n-GaN layer. Applied Physics Letters, 2010, 97, .	1.5	34
58	Room Temperature Current Injection Polariton Light Emitting Diode with a Hybrid Microcavity. Nano Letters, 2011, 11, 2791-2795.	4.5	34
59	Dislocation reduction in GaN grown on stripe patterned r-plane sapphire substrates. Applied Physics Letters, 2007, 91, 021914.	1.5	33
60	Lightâ€“Output Enhancement of Nano-Roughened GaN Laser Lift-Off Light-Emitting Diodes Formed by ICP Dry Etching. IEEE Photonics Technology Letters, 2007, 19, 849-851.	1.3	33
61	Enhancement of Light Output Intensity by Integrating ZnO Nanorod Arrays on GaN-Based LLO Vertical LEDs. Electrochemical and Solid-State Letters, 2008, 11, H84.	2.2	33
62	Characteristics of GaN-based photonic crystal surface emitting lasers. Applied Physics Letters, 2008, 93, .	1.5	32
63	High-temperature operation of GaN-based vertical-cavity surface-emitting lasers. Applied Physics Express, 2017, 10, 112101.	1.1	31
64	Phase transformation and optical characteristics of porous germanium thin film. Thin Solid Films, 2008, 516, 2934-2938.	0.8	30
65	Characteristics of Current-Injected GaN-Based Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 1594-1602.	1.9	30
66	Superior characteristics of microscale light emitting diodes through tightly lateral oxide-confined scheme. Applied Physics Letters, 2017, 110, .	1.5	30
67	Luminance Enhancement of Flip-Chip Light-Emitting Diodes by Geometric Sapphire Shaping Structure. IEEE Photonics Technology Letters, 2008, 20, 184-186.	1.3	29
68	Photogeneration of coherent shear phonons in orientated wurtzite semiconductors by piezoelectric coupling. Physical Review B, 2009, 80, .	1.1	29
69	Highly-directional emission patterns based on near single guided mode extraction from GaN-based ultrathin microcavity light-emitting diodes with photonic crystals. Applied Physics Letters, 2010, 97, .	1.5	29
70	Self-Assembled Two-Dimensional Surface Structures for Beam Shaping of GaN-Based Vertical-Injection Light-Emitting Diodes. IEEE Photonics Technology Letters, 2010, 22, 12-14.	1.3	29
71	Localized surface plasmon for enhanced lasing performance in solution-processed perovskites. Optics Express, 2016, 24, 20696.	1.7	29
72	UVA light-emitting diode grown on Si substrate with enhanced electron and hole injections. Optics Letters, 2017, 42, 4533.	1.7	29

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73	Perfect Absorption by an Atomically Thin Crystal. Physical Review Applied, 2020, 14, .	1.5	29
74	Efficiency improvement of single-junction InGaP solar cells fabricated by a novel micro-hole array surface texture process. Semiconductor Science and Technology, 2009, 24, 085007.	1.0	28
75	Development of GaN-Based Vertical-Cavity Surface-Emitting Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 850-860.	1.9	28
76	High-Performance Plasmonic Nanolasers with a Nanotrench Defect Cavity for Sensing Applications. ACS Photonics, 2018, 5, 2638-2644.	3.2	28
77	Nitride-based LEDs with nano-scale textured sidewalls using natural lithography. Nanotechnology, 2006, 17, 2998-3001.	1.3	27
78	Tunable light emissions from thermally evaporated In2O3 nanostructures grown at different growth temperatures. Journal of Crystal Growth, 2008, 310, 2264-2267.	0.7	27
79	Nanorod epitaxial lateral overgrowth of a-plane GaN with low dislocation density. Applied Physics Letters, 2009, 94, 251912.	1.5	27
80	Optical characteristics of a-plane ZnO/Zn0.8Mg0.2O multiple quantum wells grown by pulsed laser deposition. Journal of Applied Physics, 2010, 108, .	1.1	26
81	High efficiency InGaN/GaN light emitting diodes with asymmetric triangular multiple quantum wells. Applied Physics Letters, 2014, 104, .	1.5	26
82	Controllable lasing performance in solution-processed organicâ€“inorganic hybrid perovskites. Nanoscale, 2016, 8, 18483-18488.	2.8	26
83	Perovskite random lasers: a tunable coherent light source for emerging applications. Nanotechnology, 2021, 32, 282001.	1.3	26
84	InGaN self-assembled quantum dots grown by metalâ€“organic chemical vapour deposition with growth interruption. Nanotechnology, 2006, 17, 1713-1716.	1.3	25
85	Enhance light extraction of InGaN-based green LEDs by nano-imprinted 2D photonic crystal pattern. Semiconductor Science and Technology, 2008, 23, 055002.	1.0	25
86	Improving Light Output Power of the GaN-Based Vertical-Injection Light-Emitting Diodes by Mg^{+} Implanted Current Blocking Layer. IEEE Photonics Technology Letters, 2009, 21, 688-690.	1.3	25
87	Surface roughness effects on aluminium-based ultraviolet plasmonic nanolasers. Scientific Reports, 2017, 7, 39813.	1.6	25
88	Effects of Different n-Electrode Patterns on Optical Characteristics of Large-Area p-Side-Down InGaN Light-Emitting Diodes Fabricated by Laser Lift-Off. Japanese Journal of Applied Physics, 2005, 44, 7910-7912.	0.8	24
89	Emission characteristics of optically pumped GaN-based vertical-cavity surface-emitting lasers. Applied Physics Letters, 2006, 89, 121112.	1.5	24
90	Investigation of whispering gallery mode dependence on cavity geometry of quasiperiodic photonic crystal microcavity lasers. Applied Physics Letters, 2006, 89, 231111.	1.5	24

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91	High-Performance GaN-Based Vertical-Injection Light-Emitting Diodes With TiO$_{2}$â€“SiO$_{2}$ Omnidirectional Reflector and n-GaN Roughness. IEEE Photonics Technology Letters, 2007, 19, 565-567.	1.3	24
92	Enhancement of Flip-Chip Light-Emitting Diodes With Omni-Directional Reflector and Textured Micropillar Arrays. IEEE Photonics Technology Letters, 2007, 19, 1200-1202.	1.3	23
93	Optical study of a-plane InGaN/GaN multiple quantum wells with different well widths grown by metal-organic chemical vapor deposition. Journal of Applied Physics, 2008, 104, .	1.1	23
94	Numerical Study on Optimization of Active Layer Structures for GaN/AlGaN Multiple-Quantum-Well Laser Diodes. Journal of Lightwave Technology, 2008, 26, 3155-3165.	2.7	22
95	GaN-based high contrast grating surface-emitting lasers. Applied Physics Letters, 2013, 102, .	1.5	22
96	Further Enhancement of Nitride-Based Near-Ultraviolet Vertical-Injection Light-Emitting Diodes by Adopting a Roughened Mesh-Surface. IEEE Photonics Technology Letters, 2008, 20, 803-805.	1.3	21
97	Strain relaxation induced microphotoluminescence characteristics of a single InGaN-based nanopillar fabricated by focused ion beam milling. Applied Physics Letters, 2008, 93, 081110.	1.5	21
98	Highly Efficient and Bright LEDs Overgrown on GaN Nanopillar Substrates. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 971-978.	1.9	21
99	Electrically Injected GaN-Based Vertical-Cavity Surface-Emitting Lasers with TiO₂ High-Index-Contrast Grating Reflectors. ACS Photonics, 2020, 7, 861-866.	3.2	21
100	Trenched epitaxial lateral overgrowth of fast coalesced a-plane GaN with low dislocation density. Applied Physics Letters, 2006, 89, 251109.	1.5	20
101	Low Droop Nonpolar GaN/InGaN Light Emitting Diode Grown on m-Plane GaN Substrate. Journal of the Electrochemical Society, 2010, 157, H501.	1.3	20
102	Crystal quality improvement of a-plane GaN using epitaxial lateral overgrowth on nanorods. Journal of Crystal Growth, 2010, 312, 1316-1320.	0.7	19
103	High Q microcavity light emitting diodes with buried AlN current apertures. Applied Physics Letters, 2011, 99, 041101.	1.5	19
104	Characteristics of exciton-polaritons in ZnO-â€based hybrid microcavities. Optics Express, 2011, 19, 4101.	1.7	19
105	High-Temperature Polariton Lasing in a Strongly Coupled ZnO Microcavity. Applied Physics Express, 2012, 5, 082801.	1.1	19
106	Numerical analysis on current and optical confinement of III-nitride vertical-cavity surface-emitting lasers. Optics Express, 2014, 22, 9789.	1.7	19
107	Improved performance of GaN based light emitting diodes with ex-situ sputtered AlN nucleation layers. AIP Advances, 2016, 6, .	0.6	19
108	Crossover from polariton lasing to exciton lasing in a strongly coupled ZnO microcavity. Scientific Reports, 2016, 6, 20581.	1.6	19

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109	The lasing characteristics of GaN-based vertical-cavity surface-emitting laser with AlN-GaN and Ta/sub 2/O/sub 5/--SiO/sub 2/ distributed Bragg reflectors. IEEE Photonics Technology Letters, 2006, 18, 877-879.	1.3	18
110	Effect of oxygen on characteristics of nickel oxideâˆ•indium tin oxide heterojunction diodes. Journal of Applied Physics, 2006, 100, 124503.	1.1	18
111	Efficiency Enhancement of GaN-Based Power-Chip LEDs with Sidewall Roughness by Natural Lithography. Electrochemical and Solid-State Letters, 2007, 10, H59.	2.2	18
112	Efficiency enhancement of UV/blue light emitting diodes via nanoscaled epitaxial lateral overgrowth of GaN on a SiO2 nanorod-array patterned sapphire substrate. Journal of Crystal Growth, 2008, 310, 5170-5174.	0.7	18
113	Growth and characterization of a-plane AlxGa1â^'xN alloys by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2010, 312, 869-873.	0.7	18
114	Optical characteristics of a-plane InGaNâˆ•GaN multiple quantum wells with different well widths. Applied Physics Letters, 2007, 90, 181122.	1.5	17
115	Nitride-Based Thin-Film Light-Emitting Diodes With Photonic Quasi-Crystal Surface. IEEE Photonics Technology Letters, 2009, 21, 331-333.	1.3	17
116	Lasing characteristics at different band edges in GaN photonic crystal surface emitting lasers. Applied Physics Letters, 2010, 96, .	1.5	17
117	Elucidating the Physical Property of the InGaN Nanorod Light-Emitting Diode: Large Tunneling Effect. IEEE Journal of Selected Topics in Quantum Electronics, 2011, 17, 985-989.	1.9	17
118	Optical properties of (1 1Â¯ 0 1) semi-polar InGaN/GaN multiple quantum wells grown on patterned silicon substrates. Journal of Crystal Growth, 2011, 318, 500-504.	0.7	17
119	Three dimensional characterization of GaN-based light emitting diode grown on patterned sapphire substrate by confocal Raman and photoluminescence spectromicroscopy. Scientific Reports, 2017, 7, 45519.	1.6	17
120	Design of photonic crystal surface emitting lasers with indium-tin-oxide top claddings. Applied Physics Letters, 2018, 112, .	1.5	17
121	Current Modulation of Plasmonic Nanolasers by Breaking Reciprocity on Hybrid Grapheneâ€“Insulatorâ€“Metal Platforms. Advanced Science, 2020, 7, 2001823.	5.6	17
122	GaN-Based High-Q Vertical-Cavity Light-Emitting Diodes. IEEE Electron Device Letters, 2007, 28, 884-886.	2.2	16
123	Fabrication and characteristics of thin-film InGaNâ€“GaN light-emitting diodes with TiO2/SiO2omnidirectional reflectors. Semiconductor Science and Technology, 2007, 22, 831-835.	1.0	16
124	Far-Field and Near-Field Distribution of GaN-Based Photonic Crystal LEDs With Guided Mode Extraction. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1234-1241.	1.9	16
125	Study of InGaNâ€“GaN Light-Emitting Diodes With Different Last Barrier Thicknesses. IEEE Photonics Technology Letters, 2010, 22, 860-862.	1.3	16
126	Optical and Electrical Properties of GaN-Based Light Emitting Diodes Grown on Micro- and Nano-Scale Patterned Si Substrate. IEEE Journal of Quantum Electronics, 2011, 47, 899-906.	1.0	16

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127	Quaternary AlInGaN multiple quantum well 368nm light-emitting diode. Journal of Crystal Growth, 2006, 287, 582-585.	0.7	15
128	Observation of strong red photoluminescence with broadband in indium oxynitride nanoparticles. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2006, 24, 1332-1335.	0.9	15
129	Characteristics of a-plane GaN with the SiNx insertion layer grown by metal-organic chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 4972-4975.	0.7	15
130	High-Brightness InGaNâ€“GaN Flip-Chip Light-Emitting Diodes With Triple-Light Scattering Layers. IEEE Photonics Technology Letters, 2008, 20, 659-661.	1.3	15
131	Nano-Processing Techniques Applied in GaN-Based Light-Emitting Devices With Self-Assembly Ni Nano-Masks. Journal of Lightwave Technology, 2008, 26, 1445-1454.	2.7	15
132	Magnitude-tunable sub-THz shear phonons in a non-polar GaN multiple-quantum-well p-i-n diode. Applied Physics Letters, 2012, 100, .	1.5	15
133	High-Efficiency InGaN/GaN Coreâ€“Shell Nanorod Light-Emitting Diodes With Low-Peak Blueshift and Efficiency Droop. IEEE Nanotechnology Magazine, 2017, 16, 355-358.	1.1	15
134	Photonic Crystal Surface Emitting Lasers with Naturally Formed Periodic ITO Structures. ACS Photonics, 2019, 6, 684-690.	3.2	15
135	High Output Power GaN-Based Green Resonant-Cavity Light-Emitting Diodes With Trapezoidal Quantum Wells. IEEE Transactions on Electron Devices, 2020, 67, 3650-3654.	1.6	15
136	Tamm Plasmonâ€Polariton Ultraviolet Lasers. Advanced Photonics Research, 2022, 3, .	1.7	15
137	GaN-based LEDs with Al-deposited V-shaped sapphire facet mirror. IEEE Photonics Technology Letters, 2006, 18, 724-726.	1.3	14
138	Lasing characteristics of a GaN photonic crystal nanocavity light source. Applied Physics Letters, 2007, 91, .	1.5	14
139	Nano-roughening n-side surface of AlGaInP-based LEDs for increasing extraction efficiency. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2007, 138, 157-160.	1.7	14
140	High brightness GaN-based flip-chip light-emitting diodes by adopting geometric sapphire shaping structure. Semiconductor Science and Technology, 2008, 23, 025015.	1.0	14
141	Threshold gain analysis in GaN-based photonic crystal surface emitting lasers. Optics Letters, 2011, 36, 1908.	1.7	14
142	The Differences in Optical Characteristics of TiO₂and TiO₂/AAO Nanotube Arrays Fabricated by Atomic Layer Deposition. Journal of the Electrochemical Society, 2012, 159, K136-K140.	1.3	14
143	Whispering gallery mode of modified octagonal quasiperiodic photonic crystal single-defect microcavity and its side-mode reduction. Applied Physics Letters, 2006, 88, 201104.	1.5	13
144	Optical properties of In_{0.3}Ga_{0.7}N/GaN green emission nanorods fabricated by plasma etching. Nanotechnology, 2007, 18, 335706.	1.3	13

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145	Investigation of InGaN/GaN light emitting diodes with nano-roughened surface by excimer laser etching method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2007, 136, 182-186.	1.7	13
146	Enhanced Vertical Extraction Efficiency From a Thin-Film InGaNâ€“GaN Light-Emitting Diode Using a 2-D Photonic Crystal and an Omnidirectional Reflector. IEEE Photonics Technology Letters, 2008, 20, 836-838.	1.3	13
147	Output Power Enhancement of Vertical-Injection Ultraviolet Light-Emitting Diodes by GaN-Free and Surface Roughness Structures. Electrochemical and Solid-State Letters, 2009, 12, H44.	2.2	13
148	Study of the internal quantum efficiency of InGaN/GaN UV LEDs on patterned sapphire substrate using the electroluminescence method. Journal of Crystal Growth, 2011, 315, 242-245.	0.7	13
149	830-nm AlGaAs-InGaAs Graded Index Double Barrier Separate Confinement Heterostructures Laser Diodes With Improved Temperature and Divergence Characteristics. IEEE Journal of Quantum Electronics, 2013, 49, 127-132.	1.0	13
150	Quantum-Dot Surface Emitting Distributed Feedback Lasers Using Indiumâ€“Tinâ€“Oxide as Top Claddings. IEEE Photonics Technology Letters, 2016, 28, 1633-1636.	1.3	13
151	Improvement of output efficiency of p-face up photonic-crystal surface-emitting lasers. Optics Express, 2021, 29, 11293.	1.7	13
152	Hybrid Plasmonic Surface Lattice Resonance Perovskite Lasers on Silver Nanoparticle Arrays. Advanced Optical Materials, 2021, 9, 2100299.	3.6	13
153	Extraction Efficiency Enhancement of GaN-Based Light-Emitting Diodes by Microhole Array and Roughened Surface Oxide. IEEE Electron Device Letters, 2009, 30, 496-498.	2.2	12
154	Depth-resolved confocal micro-Raman spectroscopy for characterizing GaN-based light emitting diode structures. Review of Scientific Instruments, 2013, 84, 113108.	0.6	12
155	High quality factor nonpolar GaN photonic crystal nanocavities. Applied Physics Letters, 2013, 102, 191116.	1.5	12
156	Demonstration of polarization control GaN-based micro-cavity lasers using a rigid high-contrast grating reflector. Scientific Reports, 2019, 9, 13055.	1.6	12
157	Photonic integrated multiwavelength laser arrays: Recent progress and perspectives. Applied Physics Letters, 2020, 116, 180501.	1.5	12
158	Experimental and theoretical analysis on ultraviolet 370 nm AlGaInN light-emitting diodes. Semiconductor Science and Technology, 2006, 21, 598-603.	1.0	11
159	Fabrication of Microcavity Light-Emitting Diodes Using Highly Reflective AlNâ€“GaN and Ta$_{2}$O$_{5}$â€“SiO$_{2}$ Distributed Bragg Mirrors. IEEE Photonics Technology Letters, 2007, 19, 999-1001.	1.3	11
160	High-reflectivity ultraviolet AlN/AlGaN distributed Bragg reflectors grown by metalorganic chemical vapor deposition. Journal of Crystal Growth, 2008, 310, 4871-4875.	0.7	11
161	High quality ultraviolet AlGaNâˆ•GaN multiple quantum wells with atomic layer deposition grown AlGaN barriers. Applied Physics Letters, 2008, 93, 131116.	1.5	11
162	Enhanced Light Extraction in Wafer-Bonded AlGaInP-Based Light-Emitting Diodes via Micro- and Nanoscale Surface Textured. IEEE Electron Device Letters, 2009, 30, 1054-1056.	2.2	11

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163	Study of GaN-Based Photonic Crystal Surface-Emitting Lasers (PCSELs) With AlN/GaN Distributed Bragg Reflectors. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 885-891.	1.9	11
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